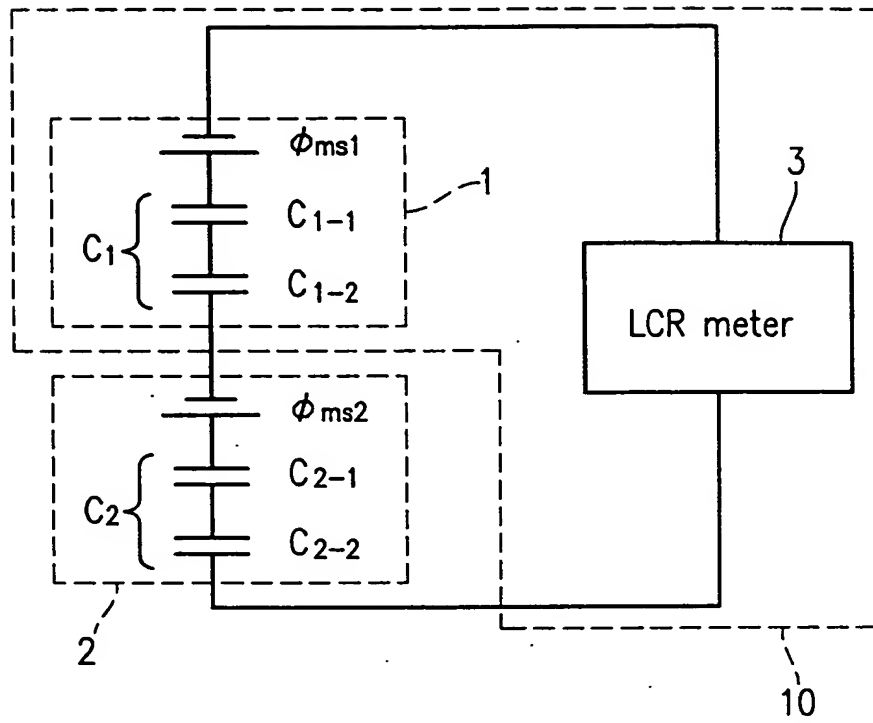


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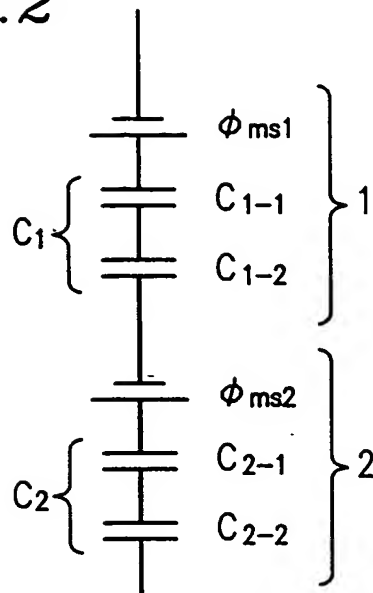
FIG. 1



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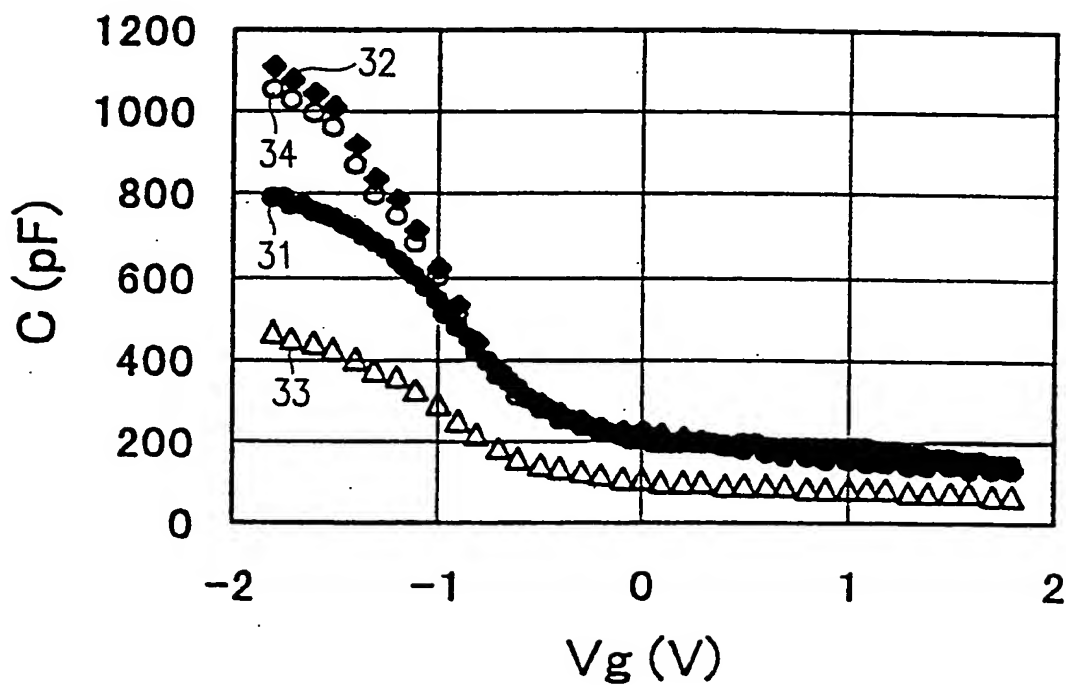
FIG. 2



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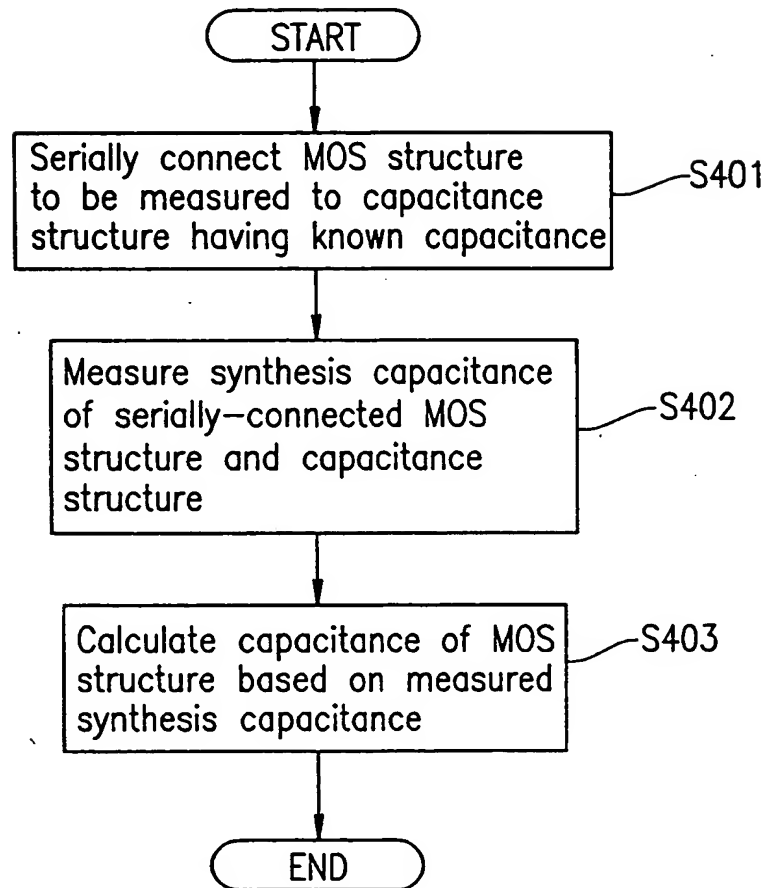
FIG. 3

NMOS C-V Characteristics



- 3.2nmC-V measured curve
- ◆— 2nmC-V ideal curve
- △— Synthesis curve
- 2nmC-V conversion curve

FIG. 4



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FIG. 5

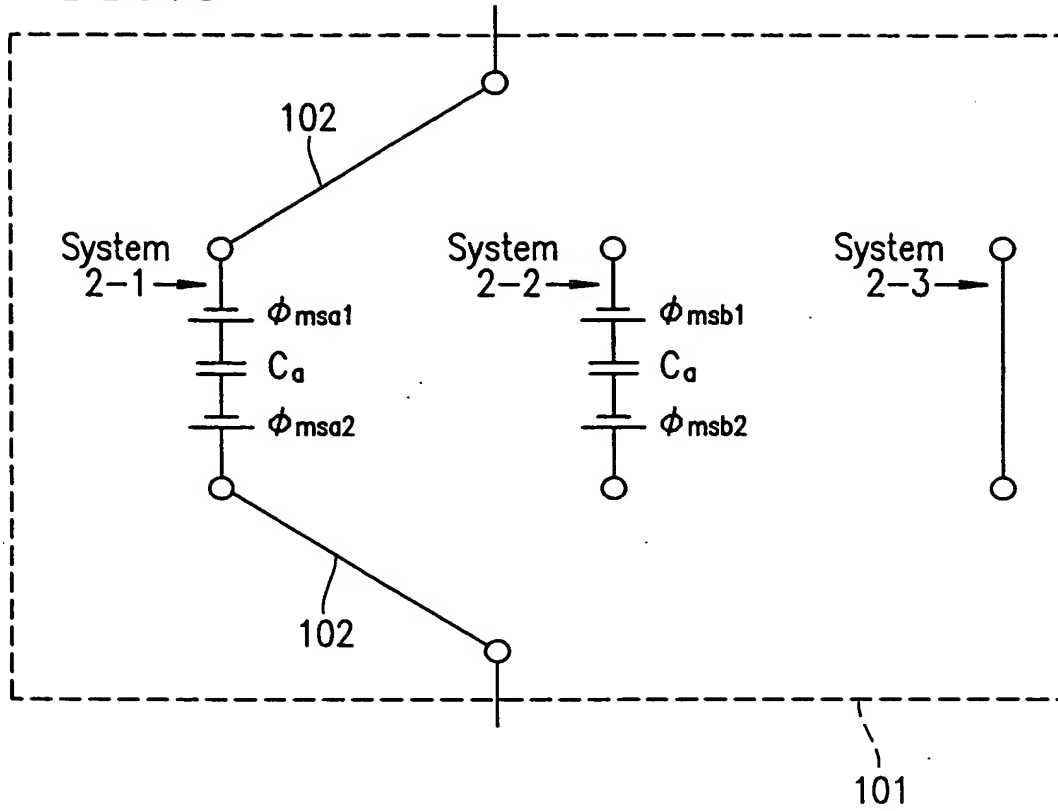
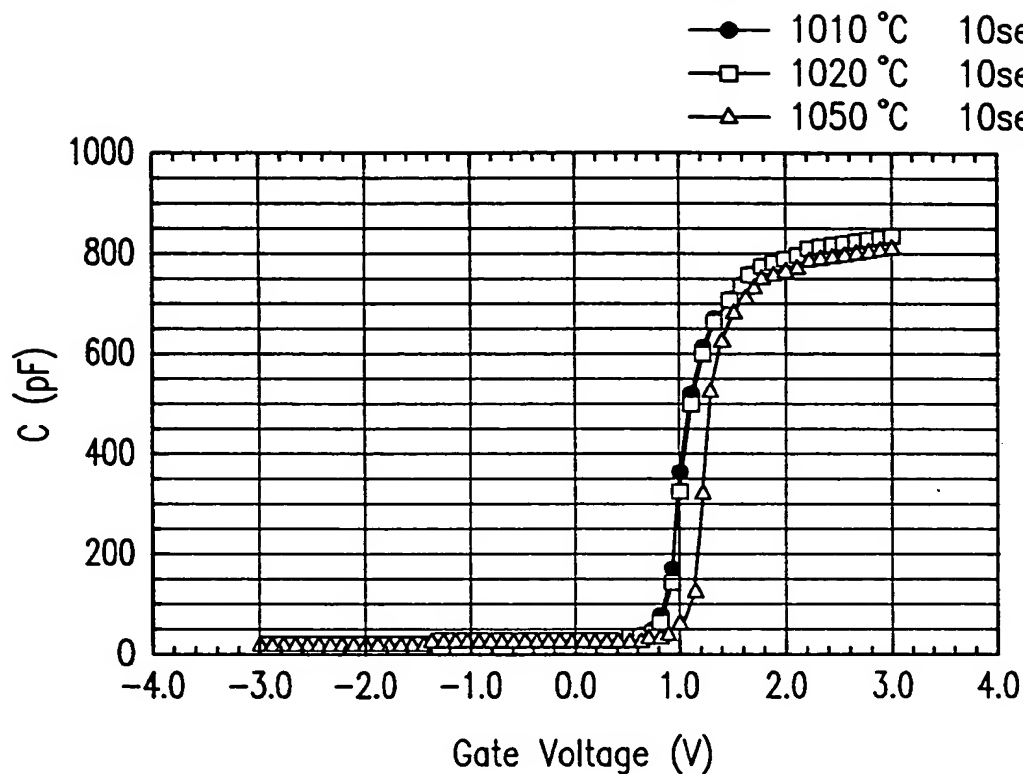


FIG. 5

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FIG. 6

PMOS C-V Characteristics



Active Area: $9\text{E}-4\text{cm}^2$

w/o Well Imp.

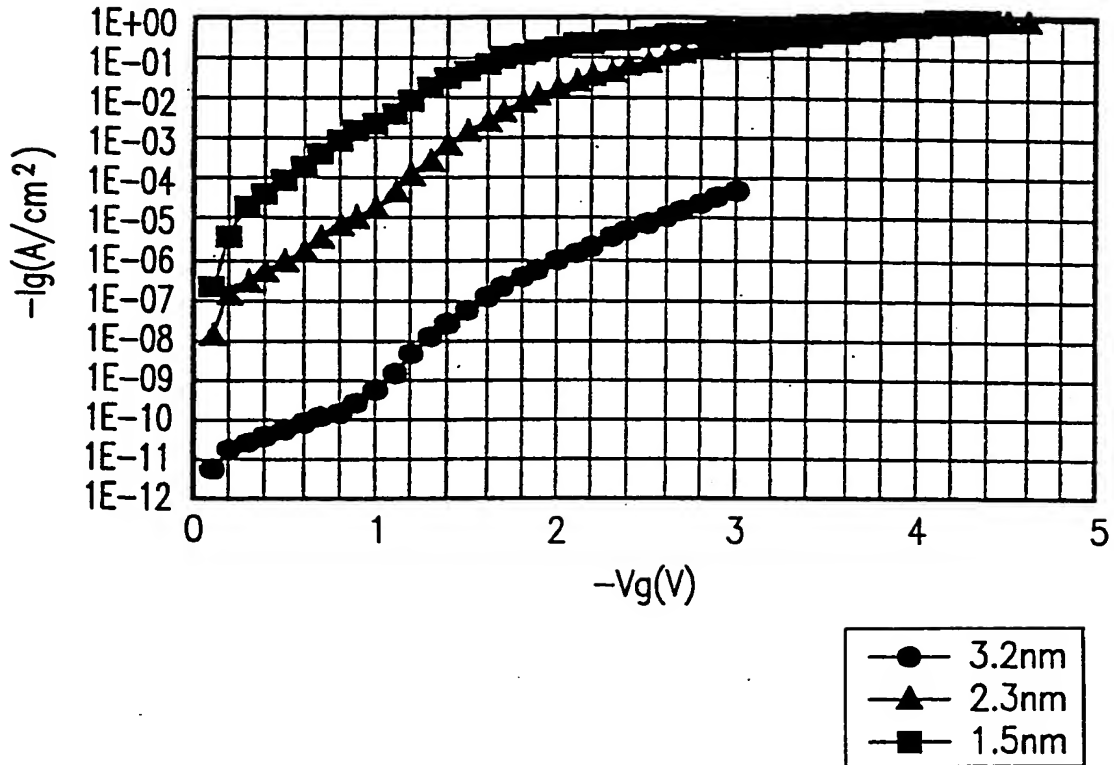
Gate SiON: NO/N_2

poly Si: 200nm

P+Imp.: BF_2

FIG. 7

NMOS I-V Characteristics

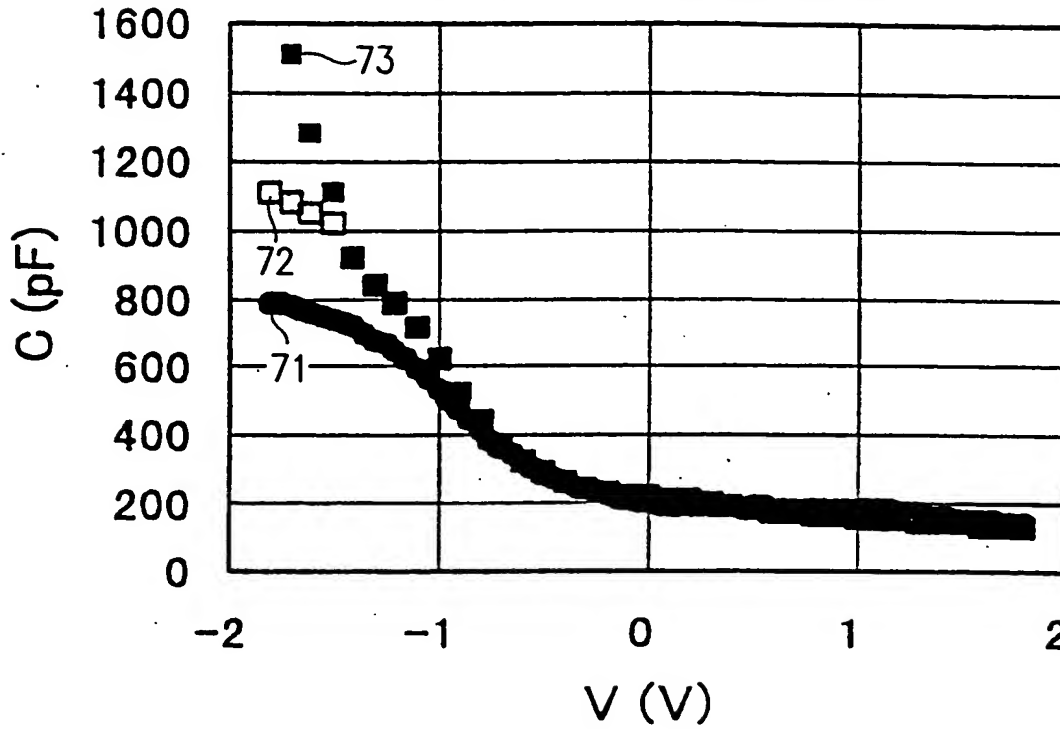


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FIG. 8

NMOS C-V Characteristics

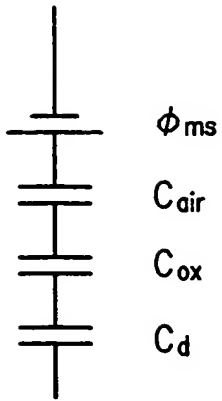


- 3.2nm C-V measured curve
- 2nm C-V ideal curve
- 2nm C-V measured curve

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FIG. 9



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